



骏业（香港）实业有限公司

400-0744-078

SOT-23 Plastic-Encapsulate Transistors

M8550 TRANSISTOR(PNP)

FEATURES

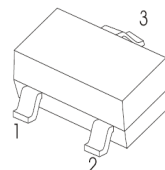
Power dissipation

MARKING: Y21

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-25	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current -Continuous	-0.8	A
P _C	Collector power dissipation	200	mW
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

SOT-23



1. BASE
2. EMITTER
3. COLLECTOR

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -100μA, I _E =0	-40		V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	I _C = -1mA, I _B =0	-25		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA, I _C =0	-6		V
Collector cut-off current	I _{CBO}	V _{CB} = -35V, I _E =0		-0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} = -20V, I _B =0		-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _C =-5mA	45		
	h _{FE(2)}	V _{CE} =-1V, I _C =-100mA	85	400	
	h _{FE(3)}	V _{CE} =-1V, I _C =-800mA	40		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -800mA, I _B =-80mA		-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-800mA, I _B =-80mA		-1.2	V
Transition frequency	f _T	V _{CE} =-6V, I _C = -20mA f=30MHz	150		MHz

* PulseTest:pulse width ≤ 300μs, duty cycle ≤2%.

CLASSIFICATION OF h_{FE(2)}

Rank	L	H
Range	85-300	300-400

Typical Characteristics

M8550

